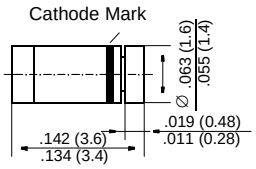
LL4448

Small Signal Diodes

MiniMELF



Dimensions in inches and (millimeters)

FEATURES

- Silicon Epitaxial Planar Diode
- Fast switching diode in MiniMELF case especially suited for automatic insertion.

- This diode is also available in other case styles including: the DO-35 case with the type designation 1N4448, the SOD-123 case with the type designation 1N4448W, and the SOT-23 case with the type designation IMBD4448.

MECHANICAL DATA

Case: MiniMELF Glass Case (SOD-80)
Weight: approx. 0.05 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Reverse Voltage	V_R	75	V
Peak Reverse Voltage	V_{RM}	100	V
Rectified Current (Average) Half Wave Rectification with Resist. Load at T_{amb} = 25 °C and f ≥ 50 Hz	I_0	150[1)]	mA
Surge Forward Current at t < 1 s and T_j = 25 °C	I_{FSM}	500	mA
Power Dissipation at T_{amb} = 25 °C	P_{tot}	500[1)]	mW
Junction Temperature	T_j	175	°C
Storage Temperature Range	T_S	–65 to +175	°C

[1)] Valid provided that electrodes are kept at ambient temperature.

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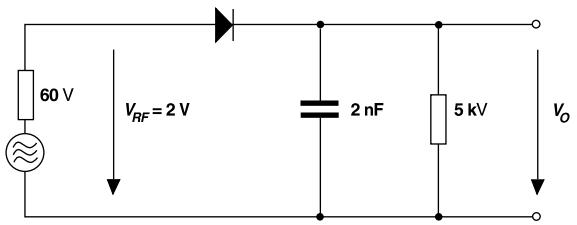
ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at I_F = 5 mA at I_F = 100 mA	 V_F V_F	 0.62 –	 – –	 0.72 1	 V V
Leakage Current at V_R = 20 V at V_R = 75 V at V_R = 20 V, T_j = 150 °C	 I_R I_R I_R	 – – –	 – – –	 25 5 50	 nA µA µA
Capacitance at $V_F = V_R = 0$	C_{tot}	–	–	4	pF
Reverse Recovery Time from I_F = 10 mA to I_R = 1 mA, V_R = 6 V, R_L = 100 Ω	t_{rr}	–	–	4	ns
Thermal Resistance Junction to Ambient Air	R_{thJA}	–	–	0.35[1)]	K/mW
Rectification Efficiency at f = 100 MHz, V_{RF} = 2 V	η_v	0.45	–	–	–

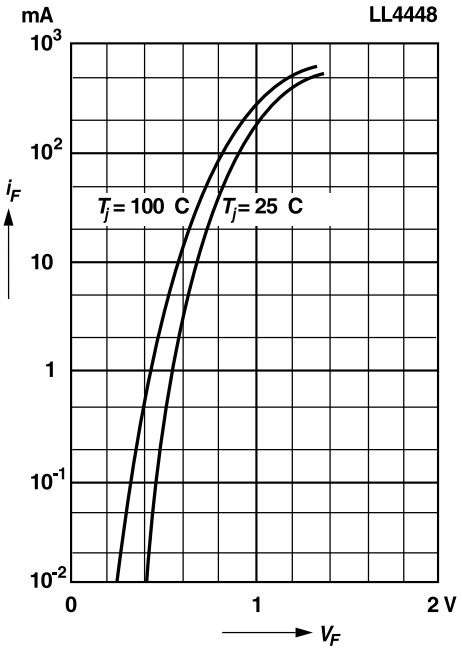
[1)] Valid provided that electrodes are kept at ambient temperature.



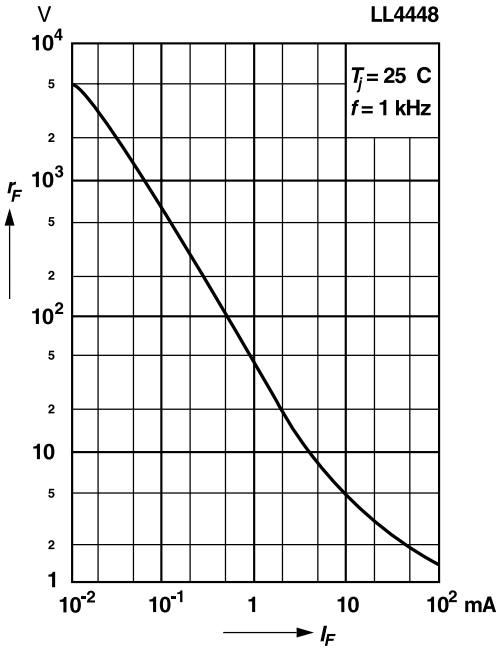
Rectification Efficiency Measurement Circuit

RATINGS AND CHARACTERISTIC CURVES LL4448

Forward characteristics

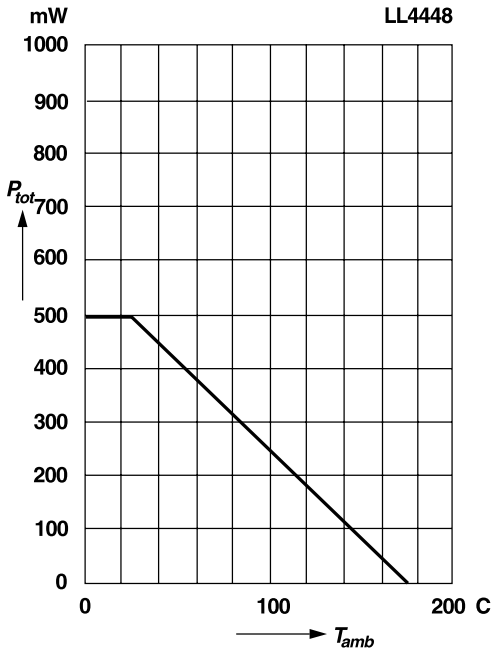


Dynamic forward resistance versus forward current

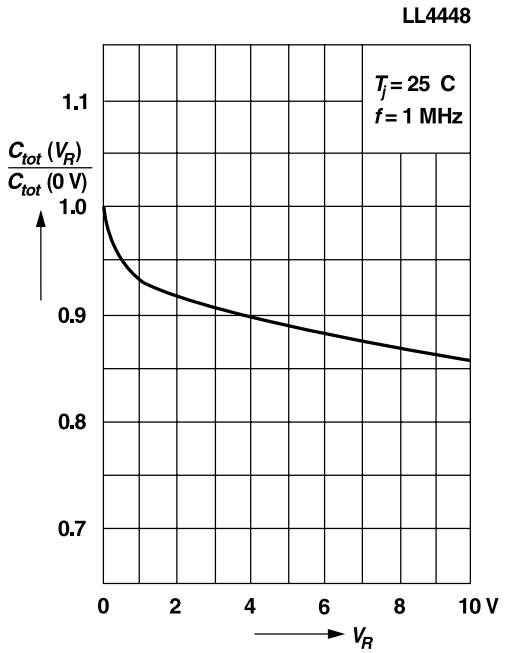


Admissible power dissipation versus ambient temperature

Valid provided that electrodes are kept at ambient temperature



Relative capacitance versus reverse voltage



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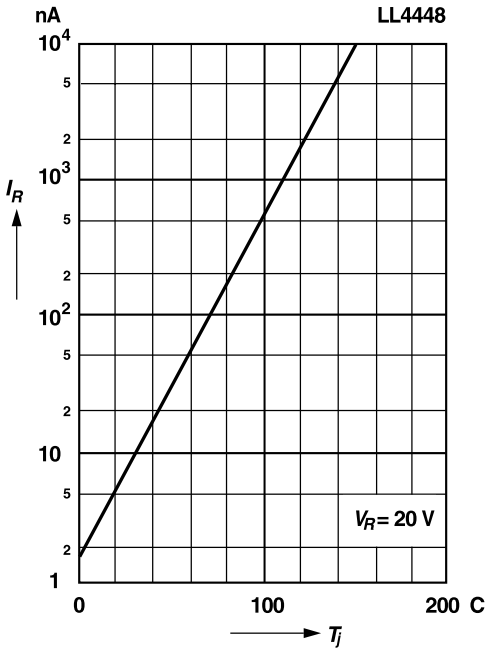
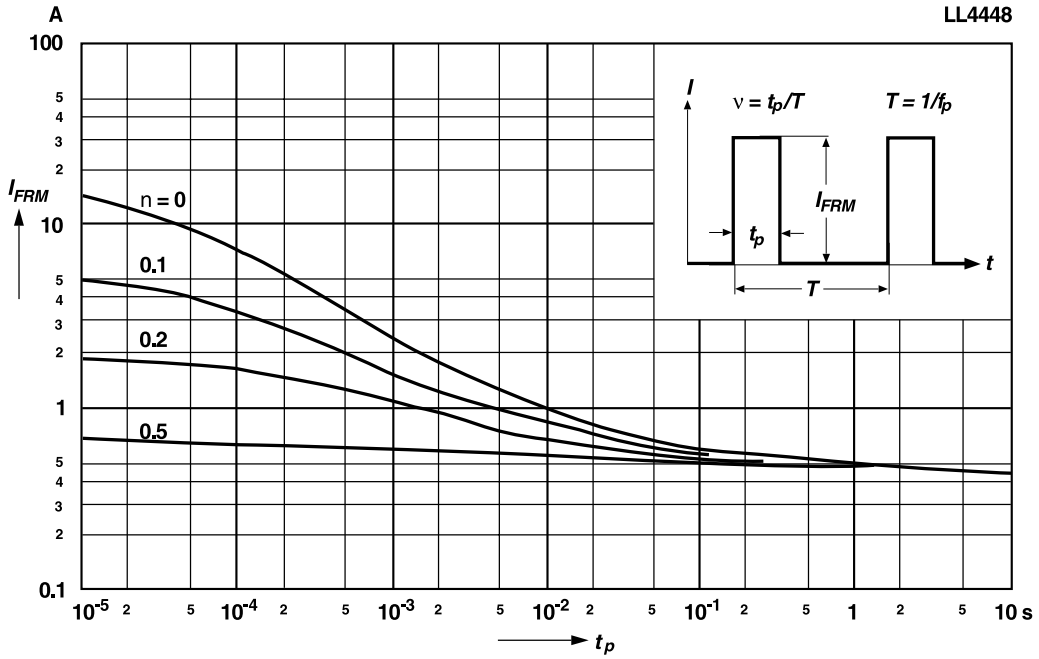
Leakage current
versus junction temperature



Admissible repetitive peak forward current versus pulse duration

Valid provided that electrodes are kept at ambient temperature



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